# 2SC5902

## Silicon NPN triple diffusion mesa type

### Horizontal deflection output for TV

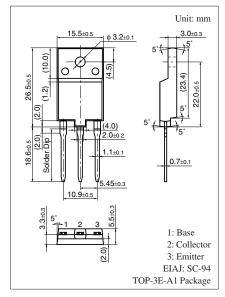
#### ■ Features

- High breakdown voltage:  $V_{CBO} \ge 1700 \text{ V}$
- Wide safe operation area
- Built-in dumper diode

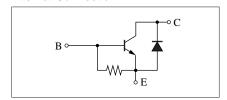
## ■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open	ı) V <sub>CBO</sub>	1700	V	
Collector-emitter voltage (E-B short	) V <sub>CES</sub>	1 700	V	
Emitter-base voltage (Collector open	ı) V <sub>EBO</sub>	7	V	
Base current	$I_{B}$	3	A	
Collector current	$I_{C}$	9	A	
Peak collector current *	$I_{CP}$	14	A	
Collector power dissipation	P <sub>C</sub>	40	W	
$T_a = 25^\circ$		3		
Junction temperature	T <sub>j</sub>	150	°C	
Storage temperature	T <sub>stg</sub>	-55 to +150	°C	

Note) \*: Non-repetitive peak collector current



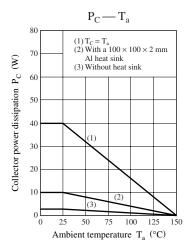
#### Internal Connection

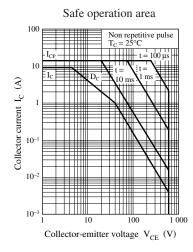


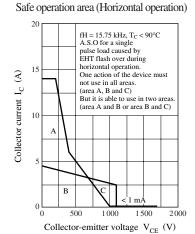
### ■ Electrical Characteristics $T_C = 25$ ° $C \pm 3$ °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Emitter-base voltage (Collector open)	$V_{EBO}$	$I_E = 500 \text{ mA}, I_C = 0$	7			V
Forward voltage	$V_F$	I <sub>F</sub> = 4.5 A			-2	V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 1000 \text{ V}, I_{E} = 0$			50	μΑ
		$V_{CB} = 1700 \text{ V}, I_E = 0$			1	mA
Forward current transfer ratio	h <sub>FE</sub>	$V_{CE} = 5 \text{ V}, I_{C} = 4.5 \text{ A}$	5		10	_
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = 4.5 \text{ A}, I_B = 1.13 \text{ A}$			3	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	$I_C = 4.5 \text{ A}, I_B = 1.13 \text{ A}$			1.5	V
Transition frequency	$f_T$	$V_{CE} = 10 \text{ V}, I_{C} = 0.1 \text{ A}, f = 0.5 \text{ MHz}$		3		MHz
Storage time	t <sub>stg</sub>	$I_C = 4.5 \text{ A}$ , Resistance loaded			5.0	μs
Fall time	t <sub>f</sub>	$I_{B1} = 1.13 \text{ A}, I_{B2} = -2.25 \text{ A}$			0.5	μs

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.







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